Part IV: one last challenge of IBS

Pairing Mechanism for FeSe systems: HEDIS (highly electron doped FeSe)

FeSe Problem ?



Single-layer FeSe/SrTiO₃, T_c>65K



One layer system. Only Electron pockets. Tc ~ 100K

Standard Paradigm of IBS: ±S-wave pairing

Different family of Fe/Pnctides n Fe/Chacogenides



Crystallographic and magnetic structures of the iron-based superconductors.

Sign-changing S-wave solutions for multi-bands + AFM interaction

±S-wave





Two band BCS gap Equation

$$\begin{aligned} \Delta_{h}(k) &= (5) \\ &- \sum_{k'} [V_{hh}(k,k')\Delta_{h}(k')\chi_{h}(k') + V_{he}(k,k')\Delta_{e}(k')\chi_{e}(k')], \\ \Delta_{e}(k) &= \\ &- \sum_{k'} [V_{eh}(k,k')\Delta_{h}(k')\chi_{h}(k') + V_{ee}(k,k')\Delta_{e}(k')\chi_{e}(k')]. \end{aligned}$$
(6)

Bulk FeSe crystal: Tc ~8K (PNAS 2008 M.K. Wu et al.)

Hanaguri, Science 2010

12 K 11 K 10 K

9 K

8 K 7 K 5 K 2.5 K 0.4 K

1.0 mV

0 T

1.0 mV

10 T

²⁰ **B**

15

-6 -4

-2

1.0 mV B

0 T

10 T

1.0 mV D

0 2 4 6

Sample bias (mV)

Tunneling conductance (nS)







k space

Tc increases by

- 1. FeSe pressure \rightarrow 37K,
- 2. Alkali element (K,Rb,Cs,Tl)doping \rightarrow 30-40K,
- 3. (LiFeOH)FeSe \rightarrow 40K,
- 4. some vacancies Fe(SeTe) \rightarrow 20K,
- 5. FeSe monolayer \rightarrow **100K**



What happens ?

- 1. Fermi surface change ? \rightarrow common
- 2. Magnetic fluc changes (AFM1, AFM2, FM) ?
- 3. Phonon ?

Heavily Electron Doped FeSe systems (X J Zhou et al) → Main change: only electron pockets





(Li_{1-x}Fe_x)OHFe_{1-y}Se, T_c=41K





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Common features: 1. No **Γ** band + **S-wave gap** on **M** band.







Key Questions: 1. Only Electron Band → how to pair ? 2. T_c (~100K) is too high.





Phonon Boost Effect for Un-conventional Superconductivity (Bang, prb 2008, 2009)

Let us separate the questions:

- 1. HEDIS with only electron pockets typically have $T_{c,max} \sim 30-40K$
- 2. FeSe monolayer with $Tc \sim 100K$ needs extra boosting mechanism.

No. 2 is simple: extra mechanism \rightarrow small angle phonon + large angle AFM repulsion

$$T_c \simeq 1.14 \; \omega_{sf}^{\tilde{\lambda}_{sf}} \cdot \omega_{ph}^{\tilde{\lambda}_{ph}} \; e^{-1/\lambda_{tot}}$$

$$\lambda_{tot} = \lambda_{sf} + \lambda_{ph}$$

$$\lambda_{sf} = \lambda_{sf} / \lambda_{tot}, \, \tilde{\lambda}_{ph} = \lambda_{ph} / \lambda_{tot}$$

Bang, prb 78, 075116 (2008); prb 79, 092503 (2009)

Effects of phonon interaction on pairing in high- T_c superconductors Isotope effect and the role of phonons in the iron-based superconductors



Both interactions utilize different mom. Spaces !!

Bang, PRB 78 (2008), 79(2009)

$$H = \sum_{k\sigma} \epsilon(k) c_{k\sigma}^{\dagger} c_{k\sigma} + \sum_{kk' \uparrow \downarrow} V_{\text{AFM}}(k,k') c_{k\uparrow}^{\dagger} c_{-k\downarrow}^{\dagger} c_{k'\downarrow} c_{-k'\uparrow},$$

Simple toy model

$$\sum_{kk'\uparrow\downarrow} V_{\rm ph}(k,k') c^{\dagger}_{k\uparrow} c^{\dagger}_{-k\downarrow} c_{k'\downarrow} c_{-k'\uparrow},$$

 $\pm S_{AFM} + S_{ph}$ wave









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Required condition: small angle phonon interaction

$T_{c}\ (\sim 100 K)$ is too high.

Evidence for small angle phonon + strong coupling



ZX Shen et al 2014







DH Lee 2015, small angle phonon scattering





More difficult question:

1. Pairing with only electron pockets : $T_{c,max} \sim 30-40K$



 $T_{c,max} \sim 30-40 K$

 $T_{c,max} \sim 30-50 K$

Pairing is possible with the same V_{sf} interaction, but **Tc should decrease**. - *Bang NJP 2014*



Electron pairing in the presence of incipient bands in iron-based superconductors





So, only Electron Band \rightarrow No problem



$$\begin{aligned} \Delta_{h}(k) &= (5) \\ &- \sum_{k'} [V_{hh}(k,k')\Delta_{h}(k')\chi_{h}(k') + V_{he}(k,k')\Delta_{e}(k')\chi_{e}(k')], \\ \Delta_{e}(k) &= \\ &- \sum_{k'} [V_{eh}(k,k')\Delta_{h}(k')\chi_{h}(k') + V_{ee}(k,k')\Delta_{e}(k')\chi_{e}(k')]. \end{aligned}$$

$$(6)$$



$$\chi_{h,e}(T) = \int_{0}^{\Lambda_{hi}} \frac{d\xi}{\xi} \tanh\left(\frac{\xi}{2T}\right) \approx \ln\left[\frac{1.14\Lambda_{hi}}{T}\right]$$
$$\chi_{e} = \int_{\epsilon_{b}}^{\Lambda_{hi}} \frac{d\xi}{\xi} \tanh\left(\frac{\xi}{2T}\right) \approx \ln\left[\frac{1.14\Lambda_{hi}}{\epsilon_{b}}\right]$$

But **Tc decreases** with sunken band for a given $V_{AFM}(Q)$





$$\tilde{\lambda}_{eff} = \left[\bar{V}_{he}N_{e}\bar{V}_{eh}N_{h}\right] \cdot \ln\left[\frac{1.14\Lambda_{hi}}{\epsilon_{b}}\right]$$

$$\tilde{\lambda}_{eff} = \sqrt{\bar{V}_{he}N_e\bar{V}_{eh}N_h}$$

Assuming only interband V_{he}

 $T_c(\epsilon_b) \approx 1.14 \Lambda_{hi} \exp\left[-1/\tilde{\lambda}_{eff}(\epsilon_b)\right]$



One problem of this incipient band model: optimal $\epsilon_{\rm b} \sim 60-80 \text{ meV}$?

In real materials, Tc $\rightarrow 0$ as $\epsilon_b \rightarrow 0$? Opposite trend to the incipient band pairing scenario.



1. \pm S-gap solution with higher Tc without impurity 2. but impurity pair-breaking effect severely suppresses Tc \rightarrow 0.



- **1.** Without impurity, T_c is lower.
- 2. ±S-gap and ++S_{ee}-gap solutions are degenerate, with the same Tc
- 3. ++**S**_{ee}-gap solution is robust against impurities.

New Concept:

Dynamical Tuning of pairing Cutoff







S-wave gap

Bare elec-elec int. is strongly repulsive.









Lowering cutoff energy $\Lambda_{\rm cut}$



 $V_{tot} < 0$ for low energy of $E < \omega_D$



Possible pairing solutions in Incipient band model



First, compared the solutions (a) and (b).



RG of V_{ab} (A)



 $\hat{V}(\Lambda) = \hat{V}^0 + \hat{V}^0 \cdot \hat{\chi}(\Lambda_{sf};\Lambda) \cdot \hat{V}(\Lambda)$

 $\hat{V}^0 = \left(egin{array}{cc} V^0_{hh} & V^0_{he} \ V^0_{eh} & V^0_{ee} \end{array}
ight)$

 $\hat{\chi}(\Lambda_{sf};\Lambda) = \left(egin{array}{cc} \chi_h & 0 \\ 0 & \chi_e \end{array}
ight)$





Now consider only two solutions:





Non-mag impurities kill only S+-_{he}-state.



Imp. Effect on \pm S-gap n ++S_{ee}-gap





Impurity pair-breaking only for \pm S-gap, ++S_{ee}-gap is robust against imp. scattering.

Three band model









$$V = \begin{bmatrix} V_{hh} & V_{he_1} & V_{he_2} \\ V_{e_1h} & V_{e_1e_1} & V_{e_1e_2} \\ V_{e_2h} & V_{e_2e_1} & V_{e_2e_2} \end{bmatrix}$$







(a)

(b)

(c)





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Varying V_{e1e2}





With non-magnetic impurities.





Figure 4 | Pressure dependence of the T_c for Tl_{0.6}Rb_{0.4}Fe_{1.67}Se₂, K_{0.8}Fe_{1.7}Se₂ and K_{0.8}Fe_{1.78}Se₂. The symbols represent the pressure-temperature

SCIENTIFIC REPORTS | 5 : 9477 | DOI: 10.1038/srep09477





Conclusions:

- 1. All HEDIS system with only electron pockets has $++S_{ee}$ -gap
- 2. FeSe monolayer is special. Need small angle phonon boost
- 3. Pairing cutoff energy is dynamically tuned by RG to $\epsilon_{\rm b}$.
- 4. $\pm S_{he}$ -pairing paradigm still governs FeSe system.





$$\begin{split} \tilde{\chi}_e(\Lambda_{sf};\Lambda) &= -T_c \sum_n 2N_e \int_{\Lambda}^{\Lambda_{sf}} d\xi \frac{\eta_v}{\tilde{\omega}_n^2 + \xi^2}, \\ \tilde{\chi}_h(\Lambda_{sf};\Lambda) &= -T_c \sum_n N_h \int_{-\Lambda_{sf}}^{-\Lambda} d\xi \frac{\eta_v}{\tilde{\omega}_n^2 + \xi^2}. \end{split}$$

When $\eta_{\nu} = \eta_1$, Cooperon is invariant w.r.t non-mag. Impurity scatt.

